DPS2021 Timetable

EST	MST	PST	GMT	CET	JST/KST	Nov.18 (Thur)		Nov.19 (Fri)	
19:00	17:00	16:00	0:00	1:00	**9:00**	Opening Remark (H Hayashi,T. Watanabe,T. Maruyama)		F-1 <Invited> Yeon Ho Im (Jeonbuk National Univ.) "Toward realistic 3D feature profile simulation on high-aspect-ratio oxide etch"	Session F Challenges to Limits for High Aspect Ratio Etching
19:10	17:10	16:10	0:10	1:10	9:10	A-1 <Invited> Luxherta Buzi (IBM Corp.) "Investigation of Plasma Etch Damage of $Ge_2Sb_2Te_5$ for Storage Class Memory and AI"	Session A Plasma Processes for New Material Devices (MRAM, Power, Organic)		
19:20	17:20	16:20	0:20	1:20	9:20				
19:30	17:30	16:30	0:30	1:30	9:30				
19:40	17:40	16:40	0:40	1:40	9:40			F-2 <Invited> Thorsten Lill (Lam Research Corp.) "Deposition and etch co-optimization to meet scaling requirements for vertically integrated memories"	
19:50	17:50	16:50	0:50	1:50	9:50	B-1 <Invited> Sumit Agarwal (Colorado School of Mines) "Selective Surface Functionalization of Si-Based Dielectrics to Enhance Selectivity During Atomic Layer Etching"	Session B Applications and Researches of Atomic Layer Controlled Etching and Deposition(ALE/ALD/Area Selective ALD)-1		
20:00	18:00	17:00	1:00	2:00	**10:00**				
20:10	18:10	17:10	1:10	2:10	10:10				
20:20	18:20	17:20	1:20	2:20	10:20			Break (& Free discussion) 20min	
20:30	18:30	17:30	1:30	2:30	10:30	Break (& Free discussion) **20min**			
20:40	18:40	17:40	1:40	2:40	10:40			F-3 Sho Kumakura (Tokyo Electron Miyagi Ltd.) "Novel Technology of High-Aspect-Ratio Etch by Utilizing Coverage Controllable Atomic Layer Deposition"	
20:50	18:50	17:50	1:50	2:50	10:50	B-2 Joseph R. Vella (Princeton Plasma Physics Laboratory) "Molecular Dynamics Study of Si-Cl-Ar Atomic Layer Etching Processes"			
21:00	19:00	18:00	2:00	3:00	**11:00**			F-4 Tomo Hasegawa (Air Liquide Laboratories K. K.) "New etchants for the etching of High Aspect Ratio (HAR) structures. Application to memory devices"	
21:10	19:10	18:10	2:10	3:10	11:10	B-3 Akiko Hirata (Sony Semiconductor Solutions Corp.) "Structural and electrical characterization of ion-induced Si damage in atomic layer etching"			
21:20	19:20	18:20	2:20	3:20	11:20			Break (& Free discussion) **10min**	
21:30	19:30	18:30	2:30	3:30	11:30	B-4 Airah Osonio (Nagoya Univ.) "Selective plasma-enhanced atomic layer etching of SiO_2 using a silane coupling agent"		Poster Sessions Part 2 Q&A **80min** **Core-time 11:30 -12:50 † Odd number**	
21:40	19:40	18:40	2:40	3:40	11:40				
21:50	19:50	18:50	2:50	3:50	11:50	C-1 Makoto Satake (Hitachi, Ltd.) "Effect of Relative Humidity on Fin Bending Mechanism During Air Exposure"	Session C Etching Technologies		
22:00	20:00	19:00	3:00	4:00	**12:00**				
22:10	20:10	19:10	3:10	4:10	12:10	Break (& Free discussion) **80min**			
22:20	20:20	19:20	3:20	4:20	12:20				
22:30	20:30	19:30	3:30	4:30	12:30				
22:40	20:40	19:40	3:40	4:40	12:40				
22:50	20:50	19:50	3:50	4:50	12:50			Break (& Free discussion) **60min**	
23:00	21:00	20:00	4:00	5:00	**13:00**				
23:10	21:10	20:10	4:10	5:10	13:10				
23:20	21:20	20:20	4:20	5:20	13:20				
23:30	21:30	20:30	4:30	5:30	13:30	D-1 Taito Yoshie (Nagoya Univ.) "Transient effects in cyclic processes on fabrications of high-aspect-ratio trenches"	Session D Modeling, Simulation and Diagnostic		
23:40	21:40	20:40	4:40	5:40	13:40				
23:50	21:50	20:50	4:50	5:50	13:50	D-2 Junghwan Um (Yonsei Univ.) "Energy dissipation on SiO_2 surface by high-energy fluorocarbon irradiation: A molecular dynamics study"		G-1 Kunihiro Kamataki (Kyushu Univ.) "Better step coverage of TEOS-PECVD SiO_2 films realized by amplitude modulation of RF discharge voltage"	Session G Deposition Technologies (CVD / PVD)
0:00	22:00	21:00	5:00	6:00	**14:00**				
0:10	22:10	21:10	5:10	6:10	14:10	D-3 Jumpei Kurokawa (Nagoya Univ.) "Random forest model for property control of plasma deposited hydrogenated amorphous carbon films"		G-2 Taishi Nojima (Hiroshima Univ.) "Growth of High Crystallinity Silicon Films by Intermittent Pulse Heating assisted Plasma Enhanced Chemical Vapor Deposition"	
0:20	22:20	21:20	5:20	6:20	14:20				
0:30	22:30	21:30	5:30	6:30	14:30	D-4 Hitoshi Tamura (Hitachi High-Tech Corp.) "Mode Transformation and Absorption of Microwaves in an Electron Cyclotron Etching Reactor"		G-3 Takayuki Matsuda (Kyoto Univ.) "Controlling of nano-network structures in BN films by a reactive plasma-assisted coating technique and the sputtering characteristics against plasma exposure"	
0:40	22:40	21:40	5:40	6:40	14:40				
0:50	22:50	21:50	5:50	6:50	14:50	Break (& Free discussion) **20min**		G-4 Yuhei Otaka (The Univ. of Tokyo) "Design of CVI Process for synthesis of SiCf/SiC Ceramics Matrix Composites from $SiCl_4$-mixed CH_3SiCl_3/H_2"	
1:00	23:00	22:00	6:00	7:00	**15:00**				
1:10	23:10	22:10	6:10	7:10	15:10	E-1 Tomohiro Kuyama (Kyoto Univ.) "Electrical characterization of exposure time dependence of plasma-induced radiation damage to SiO_2 films: Early-stage degradation turnover in the progressive phase"	Session E Surface Reaction and Damage	Break (& Free discussion) **20min**	Session H Atmospheric Pressure Plasma and Liquid Plasma
1:20	23:20	22:20	6:20	7:20	15:20				
1:30	23:30	22:30	6:30	7:30	15:30	E-2 Takashi Hamano (Kyoto Univ.) "A comprehensive analysis of defect state generation by ion bombardment at bottoms and sidewalls of deep holes in Si substrates"		H-1 Tatsuru Shirafuji (Osaka City Univ.) "Hydrophilic Treatment of Bone-Regeneration Scaffolds Using Plasma Bullets Launched from a Dielectric Surface"	
1:40	23:40	22:40	6:40	7:40	15:40				Session I Applications and Researches of Atomic Layer Controlled Etching and Deposition(ALE/ALD/Area Selective ALD) -2
1:50	23:50	22:50	6:50	7:50	15:50	E-3 Takahiro Goya (Kyoto Univ.) "A nanoindentation-based statistical evaluation scheme for mechanical property change in plasma-irradiated dielectric films"		I-1 Tomoko Ito (Osaka Univ.) "Low Energy Ion Effects in Plasma-Enhanced SiN-ALD processes"	
2:00	0:00	23:00	7:00	8:00	**16:00**				
2:10	0:10	23:10	7:10	8:10	16:10	E-4 Hojun Kang (Osaka Univ.) "Surface modification of Y_2O_3 by fluorocarbon plasmas"		I-2 Shohei Nakamura (SCREEN Holdings Co., Ltd.) "Atomic layer etching of GaN using F_2-added Ar plasma removal of BCl_3 modified layer at high temperature"	
2:20	0:20	23:20	7:20	8:20	16:20				
2:30	0:30	23:30	7:30	8:30	16:30	Break (& Free discussion) **20min**		I-3 Lamiae Hamraoui (GREMI - Université d'Orléans) "Atomic Layer Etching of Gallium Nitride (GaN) using fluorinated chemistry "	
2:40	0:40	23:40	7:40	8:40	16:40				
2:50	0:50	23:50	7:50	8:50	16:50	Award Ceremony (H Hayashi,T. Watanabe) Nishizawa Award, DPS Paper Award, Best Presentation Award, and Young Researcher Award		Break (& Free discussion) **20min**	
3:00	1:00	0:00	8:00	9:00	**17:00**				
3:10	1:10	0:10	8:10	9:10	17:10	N-1 <Nishizawa Award Lectures> Masaru Hori (Nagoya University) "Evolution of dry processes"		I-4 <Invited> Erwine Pargon (Univ. Grenoble Alpes, CNRS, LTM) "Cycling process in remote plasma source for selective etching with nanometric control"	
3:20	1:20	0:20	8:20	9:20	17:20				
3:30	1:30	0:30	8:30	9:30	17:30				
3:40	1:40	0:40	8:40	9:40	17:40	N-2 <Nishizawa Award Lectures> Olivier Joubert (LTM/CNRS) CET "Plasma Technologies for Nanoelectronics devices"			
3:50	1:50	0:50	8:50	9:50	17:50			J-1 <Invited> Rémi Dussart (GREMI - Université d'Orléans) "Plasma cryogenic etching : benefits of cooling the substrate at a low temperature in etching process technologies"	Session J Rethinking of Cryogenic Etching
4:00	2:00	1:00	9:00	10:00	**18:00**				
4:10	2:10	1:10	9:10	10:10	18:10	Break (& Free discussion) **10min**			
4:20	2:20	1:20	9:20	10:20	18:20	Poster Sessions Part 1 Q&A **80min** **Core-time 18:20 -19:40 ‡ Even number**		Closing Remark (Y. Morikawa, T. Shirafuji)	
4:30	2:30	1:30	9:30	10:30	18:30				
4:40	2:40	1:40	9:40	10:40	18:40			Free Discussion **30min**	
4:50	2:50	1:50	9:50	10:50	18:50				
5:00	3:00	2:00	10:00	11:00	**19:00**				
5:10	3:10	2:10	10:10	11:10	19:10				
5:20	3:20	2:20	10:20	11:20	19:20				
5:30	3:30	2:30	10:30	11:30	19:30				
5:40	3:40	2:40	10:40	11:40	**19:40**				
5:50	3:50	2:50	10:50	11:50	19:50				